SPECIFICATION

Product	2.13inch e-Paper	
Description	2.13" E-PAPER, B/W	
Model Name	2.13inch e-Paper v2	
Date	2019/06/13	
Revision	2.0	

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Revision History

Rev.	Issued Date	Revised Contents			
1.0	June.26.2018	Preliminary			
1.1	Dec.07.2018	ncreasing the Brand of components			
2.0	May.23.2019	Update the reliability test conditions			

1. General Description

1.1 Over View

2.13inch e-Paper is an Active Matrix Electrophoretic Display (AMEPD), with interface and a reference system design. The 2.13" active area contains 250×122 pixels, and has 1-bit B/W full display capabilities. An integrated circuit contains gate buffer, source buffer, interface, timing control logic, oscillator, DC-DC. SRAM.LUT, VCOM and border are supplied with each panel.

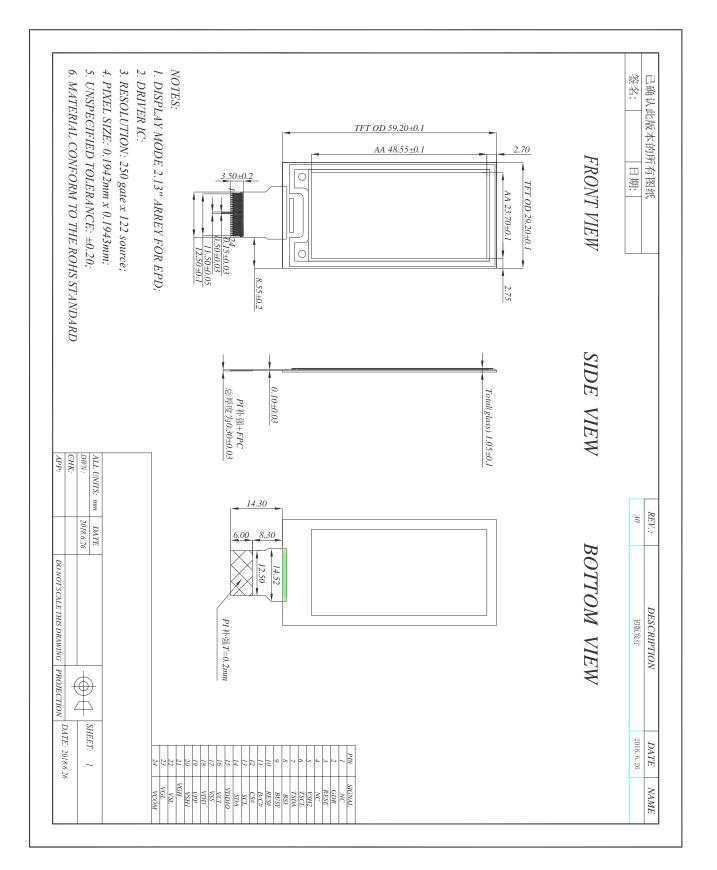
1.2 Features

- Support partial refresh
- 250×122 pixels display
- High contrast
- High reflectance
- Ultra wide viewing angle
- Ultra low power consumption
- Pure reflective mode
- Bi-stable display
- Commercial temperature range
- Landscape, portrait modes
- Hard-coat antiglare display surface
- Ultra Low current deep sleep mode
- On chip display RAM
- Low voltage detect for supply voltage
- High voltage ready detect for driving voltage
- Internal temperature sensor
- 10-byte OTP space for module identification
- Waveform stored in On-chip OTP
- Serial peripheral interface available
- On-chip oscillator
- On-chip booster and regulator control for generating VCOM, Gate and Source driving voltage

• I2C signal master interface to read external temperature sensor/built-in temperature sensor

1.3 Mechanical Specifications

Parameter	Specifications	Unit	Remark
Screen Size	2.13	Inch	
Display Resolution	122(H)×250(V)	Pixel	Dpi: 130
Active Area	23.7(H)×48.55(V)	mm	
Pixel Pitch	0.1942×0.1943	mm	
Pixel Configuration	Rectangle		
Outline Dimension	29.2(H)×59.2 (V) ×1.05(D)	mm	
Weight	3.0±0.2	g	



1.4 Mechanical Drawing of EPD module

1.5 Input/Output Terminals

Pin #	Single	ngle Description	
1	NC	No connection and do not connect with other NC pins	Keep Open
2	GDR	N-Channel MOSFET Gate Drive Control	
3	RESE	Current Sense Input for the Control Loop	
4	NC	No connection and do not connect with other NC pins e	Keep Open
5	VSH2	This pin is Positive Source driving voltage	
6	TSCL	I2C Interface to digital temperature sensor Clock pin	
7	TSDA	I2C Interface to digital temperature sensor Date pin	
8	BS1	Bus selection pin	Note 1.5-5
9	BUSY	Busy state output pin	Note 1.5-4
10	RES #	Reset	Note 1.5-3
11	D/C #	Data /Command control pin	Note 1.5-2
12	CS #	Chip Select input pin	Note 1.5-1
13	SCL	serial clock pin (SPI)	
14	SDA	serial data pin (SPI)	
15	VDDIO	Power for interface logic pins	
16	VCI	Power Supply pin for the chip	
17	VSS	Ground	
18	VDD	Core logic power pin	
19	VPP	Power Supply for OTP Programming	
20	VSH1	This pin is Positive Source driving voltage	
21	VGH	This pin is Positive Gate driving voltage	
22	VSL	This pin is Negative Source driving voltage	
23	VGL	This pin is Negative Gate driving voltage	
24	VCOM	These pins are VCOM driving voltage	

Note 1.5-1: This pin (CS#) is the chip select input connecting to the MCU. The chip is enabled for MCU communication: only when CS# is pulled LOW.

Note 1.5-2: This pin (D/C#) is Data/Command control pin connecting to the MCU. When the pin is pulled HIGH, the data will be interpreted as data. When the pin is pulled LOW, the data will be interpreted as command.

Note 1.5-3: This pin (RES#) is reset signal input. The Reset is active low.

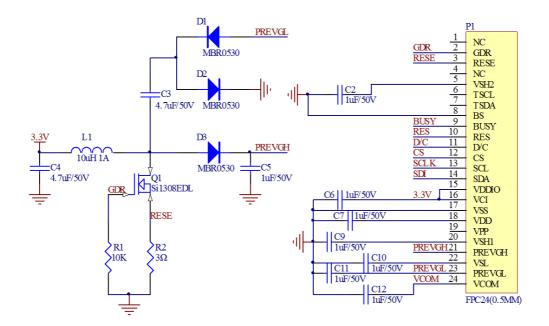
Note 1.5-4: This pin (BUSY) is Busy state output pin. When Busy is High the operation of chip should not be interrupted and any commands should not be issued to the module. The driver IC will put Busy pin High when the driver IC is working such as:

- Outputting display waveform; or

- Communicating with digital temperature sensor

Note 1.5-5: This pin (BS1) is for 3-line SPI or 4-line SPI selection. When it is "Low", 4-line SPI is selected. When it is "High", 3-line SPI (9 bits SPI) is selected.

1.6 Reference Circuit



Note :

- 1. Inductor L1 is wire-wound inductor. There are no special requirements for other parameters.
- 2. Suggests using Si1304BDL or Si1308EDL TUBE MOS (Q1) , otherwise it may affect the normal boost of the circuit.
- 3. The default circuit is 4-wire SPI. If the user wants to use 3-wire SPI.
- 4. Default voltage value of all capacitors is 50V.

2. Environmental

2.1 HANDLING, SAFETYAND ENVIROMENTAL REQUIREMENTS

WARNING

The display glass may break when it is dropped or bumped on a hard surface. Handle with care. Should the display break, do not touch the electrophoretic material. In case of contact with electrophoretic material, wash with water and soap.

CAUTION

The display module should not be exposed to harmful gases, such as acid and alkali gases, which corrode electronic components.

Disassembling the display module can cause permanent damage and invalidate the warranty agreements.

IPA solvent can only be applied on active area and the back of a glass. For the rest part, it is not allowed.

Observe general precautions that are common to handling delicate electronic components. The glass can break and front surfaces can easily be damaged. Moreover the display is sensitive to static electricity and other rough environmental conditions.

Mounting Precautions

(1) It's recommended that you consider the mounting structure so that uneven force (ex. Twisted stress) is not applied to the module.

(2) It`s recommended that you attach a transparent protective plate to the surface in order to protect the EPD. Transparent protective plate should have sufficient strength in order to resist external force.

(3) You should adopt radiation structure to satisfy the temperature specification.

(4) Acetic acid type and chlorine type materials for the cover case are not desirable because the former generates corrosive gas of attacking the PS at high temperature and the latter causes circuit break by electro-chemical reaction.

(5) Do not touch, push or rub the exposed PS with glass, tweezers or anything harder than HB pencil lead. And please do not rub with dust clothes with chemical treatment. Do not touch the surface of PS for bare hand or greasy cloth. (Some cosmetics deteriorate the PS)

(6) When the surface becomes dusty, please wipe gently with absorbent cotton or other soft materials like chamois soaks with petroleum benzene. Normal-hexane is recommended for cleaning the adhesives used to attach the PS. Do not use acetone, toluene and alcohol because they cause chemical damage to the PS.

(7) Wipe off saliva or water drops as soon as possible. Their long time contact with PS causes deformations and color fading.

Product specification The data sheet contains final product specifications.

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and dose not form part of the specification.

Product Environmental certification

ROHS

REMARK

All The specifications listed in this document are guaranteed for module only. Post-assembled operation or component(s) may impact module performance or cause unexpected effect or damage and therefore listed specifications is not warranted after any Post-assembled operation.

2.2 Reliability test

	TEST	CONDITION	METHOD	REMARK
1	High-Temperature Operation	T=50 [°] C RH=30%RH,For 240Hr	IEC 60 068-2-2Bb	
2	Low-Temperature Operation	$T = 0^{\circ}C$ for 240 hrs	IEC 60 068-2-2Ab	
3	High-Temperature Storage	T=70°C RH=40%RH For 240Hr Test in white pattern	IEC 60 068-2-2Bb	
4	Low-Temperature Storage	T = -25°C, for 240 hrs Test in white pattern	IEC 60 068-2-2Ab	
5	High Temperature, High- Humidity Operation	T=40 °C,RH=90%RH,For 168Hr	IEC 60 068-2-3CA	
6	High Temperature, High- Humidity Storage	T=60 ℃, RH=80%RH, For 240Hr Test in white pattern	IEC 60 068-2-3CA	
7	Temperature Cycle	-25 ℃ (30min)~70 ℃ (30min),100 Cycle Test in white pattern	IEC 60 068-2-14NB	
8	Package Vibration	10~500Hz Direction : X,Y,Z Duration: 1hours in each direction		
9	Package Drop Impact	Drop from height of 122 cm on Concrete surface Drop sequence:1 corner, 3edges, 6face One drop for each.	Full packed for shipment	
10	UV exposure Resistance	765 W/m²for 168hrs,40°C	IEC 60068-2-5 Sa	
11	Electrostatic discharge	Machine model: +/-250V,0Ω,200pF	IEC61000-4-2	

Actual EMC level to be measured on customer application.

Note1: Stay white pattern for storage and non-operation test.

Note2: Operation is black/white/red pattern , hold time is 150S.

Note3: The function, appearence, opticals should meet the requirements of the test before

and after the test. Note4 : Keep testing after 2 hours placing at 20 °C - 25 °C .

3. Electrical Characteristics

3.1 ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Rating	Unit			
VCI	Logic supply voltage	-0.5 to +6.0	V			
TOPR	Operation temperature range	0 to 50	°C			
TSTG	Storage temperature range	-25 to 60	°C			
-	Humidity range	40~70	%RH			

Table 3.1-1: Maximum Ratings

Note: Maximum ratings are those values beyond which damages to the device may occur. Functional operation should be restricted to the limits in the Electrical Characteristics chapter.

Note 3-1: Tstg is the transportation condition, the transport time is within 10 days for -25° C ~0°C or 50°C ~60°C.

3.2 DC CHARACTERISTICS

The following specifications apply for: VSS=0V, VCI=3.3V, TOPR=25℃.

Symbol	Parameter	Test	Applicable pin	Min.	Тур.	Max.	Unit
VCI	VCI operation voltage	-	VCI	2.2	3	3.7	V
VIH	High level input	-	SDA, SCL, CS#,	0.8VDDIO	-	-	V
VIL	Low level input voltage	-	D/C#, RES#, BS1	-	-	0.2VDDI	V
VOH	High level output	IOH = -100uA		0.9VDDIO	_	-	V
VOL	Low level output	IOL = 100uA	BUSY,	-	-	0.1VDDI	V
Iupdate	Module operating	-	-	-	4.5	-	mΑ
Isleep	Deep sleep mode	VCI=3.3V	-	-		2	uA

Table 3.2-1: DC Characteristics

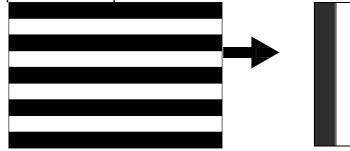
- The Typical power consumption is measured using associated 25°C waveform with following pattern transition: from horizontal scan pattern to vertical scan pattern. (Note 3-2)

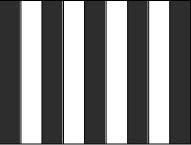
- The listed electrical/optical characteristics are only guaranteed under the controller & waveform provided by Ingcool.

- Vcom value will be OTP before in factory or present on the label sticker.

Note 3-2

The Typical power consumption





3.3 Serial Peripheral Interface Timing

The following specifications apply for: VSS=0V, VCI=2.2V to 3.7V, TOPR=25°C

Write mode

Symbol	Parameter	Min	ТурМа	x Unit
fSCL	SCL frequency (Write Mode)		20	MHz
tCSSU	Time CS# has to be low before the first rising edge of SCLK	20		ns
tCSHLD	Time CS# has to remain low after the last falling edge of SCLK	20		ns
tCSHIGH	Time CS# has to remain high between two transfers	100		ns
tSCLHIGH	Part of the clock period where SCL has to remain high	25		ns
tSCLLOW	Part of the clock period where SCL has to remain low	25		ns
tSISU	Time SI (SDA Write Mode) has to be stable before the next rising edge of SCL	10		ns
tSIHLD	Time SI (SDA Write Mode) has to remain stable after the rising edge of SCL	40		ns

Read mode

Symbol	Parameter	Min	Тур	Max	Unit
fSCL	SCL frequency (Read Mode)			2.5	MHz
tCSSU	Time CS# has to be low before the first rising edge of SCLK	100			ns
tCSHLD	Time CS# has to remain low after the last falling edge of SCLK	50			ns
tCSHIGH	Time CS# has to remain high between two transfers	250			ns
tSCLHIG	Part of the clock period where SCL has to remain high	180			ns
tSCLLOW	Part of the clock period where SCL has to remain low	180			ns
tSOSU	Time SO(SDA Read Mode) will be stable before the next rising edge of SCL		50		ns
tSOHLD	Time SO (SDA Read Mode) will remain stable after the falling edge of SCL		0		ns

Note: All timings are based on 20% to 80% of VDDIO-VSS

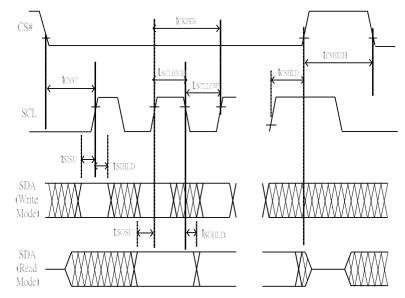


Figure 3.3-1 : Serial peripheral interface characteristics

3.4 Power Consumption

Parameter	Symbol	Conditions	TYP	Max	Unit	Remark
Panel power consumption during update	-	25°C	-	18	mAs	-
Deep sleep mode	-	25°C	-	2	uA	-

mAs=update average current \times update time

3.5 MCU Interface

3.5-1) MCU interface selection

The 2.13inch e-Paper can support 3-wire/4-wire serial peripheral interface. In the Module, the MCU interface is pin selectable by BS1 pins shown in.

Table 3.5-1: MCU Interface selection				
BS1 MPU Interface				
L 4-lines serial peripheral interface (SPI)				
Н	3-lines serial peripheral interface (SPI) - 9 bits SPI			

3.5-2) MCU Serial Peripheral Interface (4-wire SPI)

The 4-wire SPI consists of serial clock SCL, serial data SDA, D/C# and CS#, The control pins status in 4-wire SPI in writing command/data is shown in Table 7- 2and the write procedure 4-wire SPI is shown in Figue 7-2.

Table 3.5-2 : Control pins status of 4-wire SPI

Function	SCL pin	SDA pin	D/C# pin	CS# pin
Write	1	Command bit	L	L
Write data	1	Data bit	Н	L

Note:

- (1) L is connected to VSS and H is connected to VDDIO
- (2) † stands for rising edge of signal

In the write mode, SDA is shifted into an 8-bit shift register on each rising edge of SCL in the order of D7, D6, ... D0. The level of D/C# should be kept over the whole byte. The data byte in the shift register is written to the Graphic Display Data RAM (RAM)/Data Byte register or command Byte register according to D/C# pin.

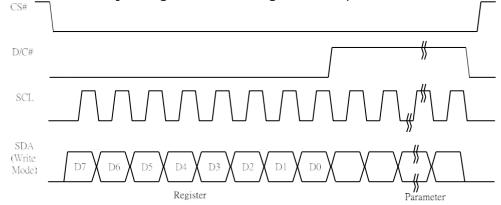


Figure 3.5-1: Write procedure in 4-wire SPI mode

In the Read mode:

- 1. After driving CS# to low, MCU need to define the register to be read.
- SDA is shifted into an 8-bit shift register on each rising edge of SCL in the order of D7, D6, ... D0 with D/C# keep low.
- 3. After SCL change to low for the last bit of register, D/C# need to drive to high.
- 4. SDA is shifted out an 8-bit data on each falling edge of SCL in the order of D7, D6, ... D0.
- 5. Depending on register type, more than 1 byte can be read out. After all byte are read, CS# need to drive to high to stop the read operation.

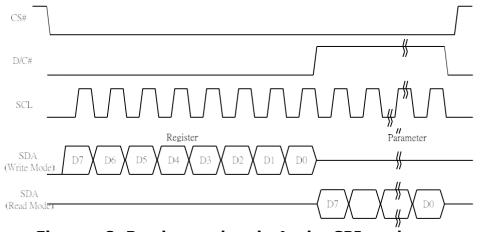


Figure v-2: Read procedure in 4-wire SPI mode

3.5-3) MCU Serial Peripheral Interface (3-wire SPI)

The 3-wire SPI consists of serial clock SCL, serial data SDA and CS#. The operation is similar to 4-wire SPI while D/C# pin is not used and it must be tied to LOW. The control pins status in 3-wire SPI is shown in Table 7-3.

Function	SCL pin	SDA pin	D/C# pin	CS# pin
Write	1	Command bit	Tie LOW	L
Write data	1	Data bit	Tie LOW	L

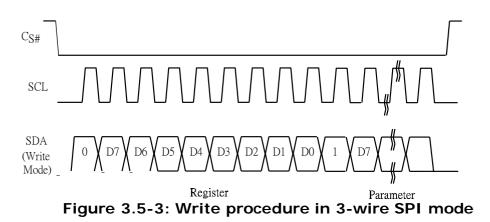
Table 3.5-3 : Control pins status of 3-wire SPI

Note:

(1)L is connected to VSS and H is connected to VDDIO

(2) stands for rising edge of signal

In the write operation, a 9-bit data will be shifted into the shift register on each clock rising edge. The bit shifting sequence is D/C# bit, D7 bit, D6 bit to D0 bit. The first bit is D/C# bit which determines the following byte is command or data. When D/C# bit is 0, the following byte is command. When D/C# bit is 1, the following byte is data. shows the write procedure in 3-wire SPI



In the Read mode:

- 1. After driving CS# to low, MCU need to define the register to be read.
- 2. D/C = 0 is shifted thru SDA with one rising edge of SCL
- 3. SDA is shifted into an 8-bit shift register on each rising edge of SCL in the order of D7, D6, ... D0.
- 4. D/C#=1 is shifted thru SDA with one rising edge of SCL
- 5. SDA is shifted out an 8-bit data on each falling edge of SCL in the order of D7, D6, ... D0.
- 6. Depending on register type, more than 1 byte can be read out. After all byte are read, CS# need to drive to high to stop the read operation.

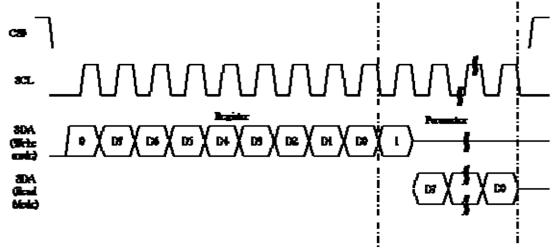


Figure **3.5**-3: Read procedure in 3-wire SPI mode

3.6 Temperature sensor operation

Following is the way of how to sense the ambient temperature of the module. First, use an external temperature sensor to get the temperature value and converted it into HEX format with below mapping table, then send command 0x1A with the HEX temperature value to the module thru the SPI interface.

The temperature value to HEX conversion is as follow:

1. If the Temperature value MSByte bit D11 = 0, then

The temperature is positive and value (DegC) = + (Temperature value) / 16

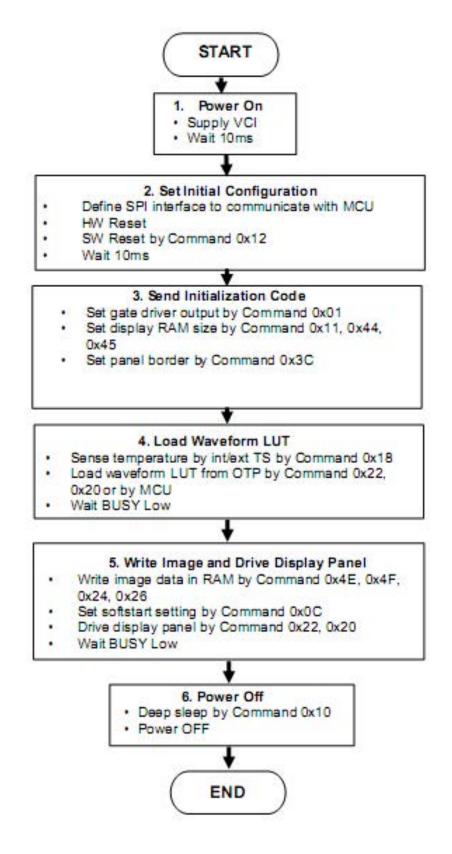
2. If the Temperature value MSByte bit D11 = 1, then

The temperature is negative and value (DegC) = \sim (2's complement of Temperature value) / 16

12-bit binary (2's complement)	Hexadecimal Value	Decimal Value	Value [DegC]
0111 1111 0000	7F0	2032	127
0111 1110 1110	7EE	2030	126.875
0111 1110 0010	7E2	2018	126.125
0111 1101 0000	7D0	2000	125
0001 1001 0000	190	400	25
0000 0000 0010	002	2	0.125
0000 0000 0000	000	0	0
1111 1111 1110	FFE	-2	-0.125
1110 0111 0000	E70	-400	-25
1100 1001 0010	C92	-878	-54.875
1100 1001 0000	C90	-880	-55

4. Typical Operating Sequence

4.1 Normal Operation Flow



5. COMMAND TABLE

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	01	01	0	0	0	0	0	0	1	Driver	Gate setting
0	1		A7	A6	A5	A4	A3	A2	A1	AO	Output	A[8:0]= 127h [POR], 296 MUX
0	1		0	0	0	0	0	0	0	A8	control	MUX Gate lines setting as (A[8:0] + 1)
0	1		0	0	0	0	0	B2	B1	BO		B[2:0] = 000 [POR]. B[2:0] = 000 [POR]. Gate scanning sequence and direction B[2]: GD Selects the 1st output Gate GD=0 [POR], G0 is the 1st gate output channel, gate output sequence is G0,G1, G2, G3, . GD=1, G1 is the 1st gate output channel, gate output sequence is G1, G0, G3, G2, . B[1]: SM Change scanning order of gate driver SM=0 [POR], G0, G1, G2, G3295 (left and right gate interlaced) SM=1, G0, G2, G4G294, G1, G3,G295 B[0]: TB TB = 0 [POR], scan from G0 to G295 TB = 1, scan from G295 to G0.
												,
0	0	03	0	0	0	0	0	0	1	1	Gate	Set Gate driving voltage
0	1		0	0	0	A4	A3	A2	A1	AO	Driving	A[4:0] = 00h [POR]
											voltage	VGH setting from 12V to 20V
											Control	A[4:0] VGH A[4:0] VGH
												07h 12 10h 16.5
												08h 12.5 11h 17
												09h 13 12h 17.5
												0Ah 13.5 13h 18
												0Bh 14 14h 18.5
												0Ch 14.5 15h 19
												0Dh 15 16h 19.5
												0Eh 15.5 17h 20
												0Fh 16 Other NA

<u>?/W#</u>		Hex	D7	D6	D5	D4	D3	D2	D1	DO		Command			Descript	ion	[7 0]
0	0	04	0	0	0	0	0	1	0	(~	Source				voltage A	
0	1		A7 B7	A6 B6	A5 B5	A4 B4	A3 B3	A2 B2	A1 B1	A0 B0	— C	Driving				0V B[7:0] 7:0] = 32	
0	1		C7	C6	C5	C4	C3	C2	C1	CO		/oltage	[POR], \			.0] = 52	
[_] (D]											C	Control					
	7] = 1, SH2 volt	200 50	tting	from 2) /\/ +/			/B[7] = 1 /\/SLI		tago	cotti	ng from 9\	/ to 17\/] = 0,	rom 0 V	to 17)
A/B[7	VSH1/V	SH A	/B[7:	VSH1			v 311	1/ 0311	2 001	laye	settii	ng nom 4v	10 17 0	VJL	setting i	0111 - 7 V	10-170
:0]	2	0		2			۸/D[.	7 VSH1	/ ^	/B[7	VCL	1			C[7:0]	VSL]
8Eh	2.4	AI	-h	5.7			:0]	VSH2		0]	1/V				1Ah	-9	-
8Fh	2.5	B	Dh	5.8			_				H2						-
90h	2.6	B	1h	5.9			23h	9	3	Ch	14				1Ch	-9.5	
91h	2.7	B	2h	6			24h	9.2	3	Dh	14.2	2			1Eh	-10	
92h	2.8	B	3h	6.1			25h	9.4	3	Eh	14.4	4			20h	-10.5	
93h	2.9	B	4h	6.2			26h	9.6	3	Fh	14.0	6			22h	-11	
94h	3		5h	6.3			27h	9.8	4	0h	14.8	8			24h	-11.5	
	3.1		5h	6.4			28h	10	4	1h	15				26h	-12	
95h	3.1			6.5			29h	10.2	4	2h	15.2	2			28h	-12.5	
96h			7h				2Ah	10.4		3h	15.4				2Ah	-13	
97h	3.3		3h	6.6			2Bh	10.6		4h	15.0				2Ch	-13.5	-
98h	3.4	B	9h	6.7			2Ch	10.8		5h	15.8				2Eh	-14	-
99h	3.5	B	۹h	6.8							_	8			30h	-14.5	-
9Ah	3.6	BI	3h	6.9			2Dh	11		6h	16						
9Bh	3.7	B	Ch	7			2Eh	11.2		7h	16.2				32h	-15	
9Ch	3.8	BI	Dh	7.1			2Fh	11.4	4	8h	16.4	4			34h	-15.5	
9Dh	3.9	BI	Eh	7.2			30h	11.6	4	9h	16.0	6			36h	-16	
9Eh	4		-h	7.3			31h	11.8	4	Ah	16.8	8			38h	-16.5	
9Fh	4.1		Dh	7.4			32h	12	4	Bh	17				3Ah	-17	
A0h	4.2		1h	7.5			33h	12.2	C	ther	NA				Other	NA	
							34h	12.4							I	I	1
A1h	4.3		2h	7.6													
A2h	4.4		3h	7.7			35h	12.6									
A3h	4.5	C4	4h	7.8			36h	12.8									
A4h	4.6	C!	ōh	7.9			37h	13									
A5h	4.7	Ce	5h	8			38h	13.2									
A6h	4.8	C	7h	8.1			39h	13.4									
A7h	4.9	C	3h	8.2			3Ah	13.6									
A8h	5	C	9h	8.3		-	3Bh	13.8									
A9h	5.1	C	۹h	8.4		_	L]					
AAh	5.2		3h	8.5		-											
ABh	5.3		Ch	8.6		-											
ACh	5.4		Dh	8.7		_											
						_											
ADh	5.5		Eh	8.8		_											
AEh	5.6	0	ther	NA													

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	08	0	0	0	0	1	0	0	0		Program User Command Setting
												The command required CLKEN=1.
												Refer to Register 0x22 for detail.
												BUSY pad will output high during operation.
											T	
0	0	09	0	0	0	0	1	0	0	1	Write Register	Write Register for User Command
0	1		A7	A6	A5	A4	A3	A2	A1	AO	for User	Selection
0	1		B7	B6	B5	B4	B3	B2	B1	BO	Command	A[7:0] ~ D[7:0]: Reserved
0	1		C7	C6	C5	C4	C3	C2	C1	CO		Details refer to Application Notes of
0	1		D7	D6	D5	D4	D3	D2	D1	DO		User Command Setting
0	0	0A	0	0	0	0	1	0	1	0	Read Register	Read Register for User Command
											for User	
											Command	

0 0 0 0 1 1 0 0 Booster foot and Phase 3 for sort start current and duration start start current and duration start current and duration start current and duration start start current and duration start current and duration start current and duration start start current and duration start current and duration start start current and duration start current and duratin start curre	R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Command		Description
0 1 1 66 86 81 82 Control 0 1 0 66 C5 C4 C3 C2 C1 C0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 0 0 D1 D2	0	0		0	0	0	0	1	1	0	0	Booster Soft		able with Phase 1, Phase 2
0 1 1 C6 C5 C4 C3 C2 C1 C0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 0 0 D5 D4 D3 D2 D1 D0 0 1 1 0 1 0 1 <						A5		A3						
0 1 0 0 D5 D4 D3 D2 D1 D0 B(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> Soft start satting for Phase -> C(P(POR) C(7.0) -> C(7.0) -> C(7.0								<u>сз</u>				CONTROL	A[7:0] -> 9	for start setting for Phase1
						D5	D4					1		= 8Bh [POR]
C17.0] - S oft start setting for Phase - 6 06 (POR) D17.0] -> Duration setting D17.0] -> Duration setting Bit Description of each byte: ML6.01 / BL6.01 / C16.01. Bit (6.4) D10 3 011 4 100 5 101 6 101 6 101 6 010 3 011 4 100 5 101 6 010 3 011 4 100 5 101 6 0101 32 0110 33 0101 32 0110 33 0101 32 0111 4 1000 5.4 1011 <t< td=""><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td>B[7:0] -> S</td><td>oft start setting for Phase2</td></t<>													B[7:0] -> S	oft start setting for Phase2
= 9 % I [POR] D[7:0] -> Duration setting = 0'h [POR] Bit Description of each byte: Alc:0] / B[6:0] / C[6:0]: Bit(5:4] D'(Veakest) 000 100 3 101 4 100 5 101 6 110 7													$C[7\cdot 0] \rightarrow S$	
- orh [Po8] Bit Description of each byte: AL:0.7 / BIs:01 / CI6:01: Bit(6:4) Driving Strength Selecti 000 001 2 010 3 011 4 100 5 101 6 110 7 Bit(3:0) Min Off Time Setting of GDR [Time unit] 0000:001 NA 100 2.6 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.4 1001 7.3 1001 1.5 1101 1.8 1101<													0[7:0] > 0	
Bit Description of each tyte: AI: 01 / Bit(5:4) Driving Strength 000 1(Weakest) 001 2 010 3 011 4 100 5 101 6 100 5 101 6 100 5 101 6 100 2 010 3 101 6 100 5 101 6 100 2 0000 2.6 0101 3.9 0101 3.9 0101 3.9 0101 3.9 0101 3.9 0101 3.9 0101 3.9 0101 3.4 1000 5.4 1001 1.5 1010 1.8 1011 1.4 1000 9.8 1001 1.8 1010 1.8 1011 1.6													D[7:0] -> D	
Alf-c:01 / Zff-c:01 / Zff-c:01 Bit[6:4] Diving Strength Selecti 000 000 1 (Weakest) 001 2 010 3 011 4 100 5 101 6 110 7 Bit[3:0] Min Off Time Setting of GDR [Time unit] 0000 2.6 0101 3.2 0101 3.2 0101 3.2 0101 3.9 0111 4.6 1000 2.6 0101 3.2 0101 3.2 0101 3.2 0101 3.2 0101 3.9 0111 4.6 1000 5.4 1001 1.5 1101 1.5 1101 1.5 1101 1.5 1101 1.5 1101 1.5 1101 1.5 <tr< td=""><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td>Bit Descript</td><td></td></tr<>													Bit Descript	
Selecti 000 1(Weakest) 001 2 010 3 011 4 100 5 101 6 110 7 Bit(30) Min Off Time Setting of GDR [Time unit] 0000-001 NA 0100 2.6 0101 3.9 0111 4.6 1000 5.4 1000 5.4 1001 6.3 1010 7.3 1010 15.4 1010 15.4 1010 15.8 1111 16.5 1101 11.5 1110 13.8 1111 16.5 1101 13.8 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111													A[6:0] / B[0	6:0] / C[6:0]:
000 1(Weakest) 001 2 010 3 011 4 100 5 101 6 110 7 Bit(3:0) Min Off Time Setting of GDR [Time unit] 0000-001 1 1 NA 0100 2.2 0110 3.2 0110 3.2 0111 4.6 1000 5.4 1011 4.6 1000 5.4 1011 8.4 1100 9.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1111 16.5 1111 16.5 1													Bit[6:4]	
001 2 010 3 011 4 100 5 101 6 110 7 Bit(3:0) Min Off Time Setting of GDR [Time unit] 0000 2.6 0101 3.9 0111 4.6 1000 5.4 1001 6.3 1011 4.6 1000 5.4 1001 6.3 1011 8.4 1000 9.8 1101 11.5 1101 11.5 1101 13.8 1101 13.8 1101 14.6 1000 9.8 1101 11.5 1101 13.8 1101 13.8 1101 13.8 1101 14.5 1101 15.4 1000 9.8 1111 16.5 D[5:0]: duration setting of phase 2 <													000	
010 3 011 4 100 5 101 6 110 7 Bit(30) GB (Time unit) 0000-001 1 NA 0000 010 3.2 0100 2.6 0101 3.2 0101 3.2 0111 4.6 1000 5.4 1001 6.3 1011 8.4 1001 6.3 1011 8.4 1100 9.8 1111 16.5 015:0]: duration setting of phase 2 016:4]: duration setting of phase 2 017:0]: duration setting of phase 2 0[1:0]: duration setting of phase 2 0[1:0]: duration setting of phase 1 Bit[1:0] Burtino f Phase (Approximation) 00 10ms 01 20ms														
011 4 100 5 101 6 110 7 Bit(3:0) Min Off Time Setting of GDR [Time unit] 0000-001 1 10 NA 010 3.2 0111 4.6 1001 3.2 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 112.1 duration setting of phase 2 11:0]: duration setting of phase 1 11:0]: duration setting of phase 2 11:0]: duration of Phase [Appproximation] 00 <td></td>														
100 5 101 6 110 7 Bit(3:0) Min Off Time Setting of GDR [Time unit] 0000-001 1 1 NA 0100 2.6 0101 3.2 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1111 16.5 015:0]: duration setting of phase 3 013:2]: duration setting of phase 3 013:2]: duration setting of phase 3 014:20:10: duration setting of phase 1 115:0]: duration setting of phase 1 116:0] Puration of Phase 1 117:0] Puration of Phase 1 118:[1:0] Puration of Phase 1 100 10ms 00 10ms														
ID1 6 I10 7 Bit(3:0) Min Off Time Setting of GDR [Time unit] 0000 01 1 NA 0100 2.6 0101 3.2 0110 3.9 0111 4.6 1000 5.4 1010 6.3 1011 8.4 1100 9.8 1011 8.4 1100 9.8 1011 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 11110 13.8														
110 7 Bit(3:0) Min Off Time setting of GDR [Time unit] 0000-001 N 1 NA 0100 2.6 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1000 9.8 1101 11.5 1101 13.8 1110 13.8 1111 16.5														
Bit(3.0) Min Off Time Setting of GDR [Time unit] 0000-001 NA 0100 2.6 0101 3.2 0110 3.9 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1101 13.8 1111 16.5 D[5:0]: duration setting of phase D[5:4]: duration setting of phase 2 D[1:0]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Duration of Phase 1 [Approximation] 00 10ms 01 20ms														
bit(3.0) GDR [Time unit] 0000-01 NA 0100 2.6 0101 3.2 0110 3.9 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1110 13.8 1111 16.5													110	1
I NA 0100 2.6 0101 3.2 0110 3.9 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1101 11.5 1101 13.8 1111 16.5 D[5:0]: duration setting of phase 3 D[3:2]: duration setting of phase 3 D[3													Bit[3:0]	Min Off Time Setting of GDR [Time unit]
0101 3.2 0110 3.9 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1110 13.8 1111 16.5 D[5:0]: duration setting of phase 2 D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 1 Bit[1:0] puration of Phase [Approximation] 00 10ms 01 20ms														NA
0101 3.2 0110 3.9 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1110 13.8 1111 16.5 D[5:0]: duration setting of phase 2 D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 1 Bit[1:0] puration of Phase [Approximation] 00 10ms 01 20ms													0100	2.6
0110 3.9 0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1101 11.5 1101 13.8 1111 16.5 D[5:0]: duration setting of phase D[5:1]: duration setting of phase 3 D[5:2]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Duration of Phase [Approximation] 00 10ms 01 20ms													0101	3.2
0111 4.6 1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1101 11.5 1101 13.8 1111 16.5 D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[5:4]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Duration of Phase [Approximation] 00 10ms 01 20ms														
1000 5.4 1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1110 13.8 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 1111 16.5 112 duration setting of phase 3 D[5:0]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] puration of Phase [Approximation] 00 01 20ms													0111	4.6
1001 6.3 1010 7.3 1011 8.4 1100 9.8 1101 11.5 1101 13.8 1111 16.5 D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Duration of Phase [Approximation] 00 10ms 01 20ms													1000	
1010 7.3 1011 8.4 1100 9.8 1101 11.5 1101 13.8 1111 16.5 D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Puration of Phase [Approximation] 00 10ms 01 20ms														
1011 8.4 1100 9.8 1101 11.5 1110 13.8 1111 16.5 D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[5:4]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Duration of Phase [Approximation] 00 10ms 01 20ms														
1100 9.8 1101 11.5 1101 13.8 1111 16.5 D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 1 Bit[1:0] Duration of Phase [Approximation] 00 10ms 01 20ms													1011	
1101 11.5 1110 13.8 1111 16.5 D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Puration of Phase [Approximation] 00 10ms 01 20ms														
111013.8111116.5D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 2 D[1:0]: duration setting of phase 1Bit[1:0]Duration of Phase [Approximation]0010ms0120ms														
1111 16.5 1111 16.5 D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Duration of Phase [Approximation] 00 10ms 01 20ms														
D[5:0]: duration setting of phase D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 2 D[1:0]: duration setting of phase 1Bit[1:0]Duration setting of phase phase 1Bit[1:0]Duration of Phase [Approximation]0010ms 010120ms														
D[5:4]: duration setting of phase 3 D[3:2]: duration setting of phase 2 D[1:0]: duration setting of phase 1 Bit[1:0] Duration of Phase [Approximation] 00 10ms 01 20ms														10.5
[Approximation] 00 10ms 01 20ms													D[5:4]: dur D[3:2]: dur	ation setting of phase 3 ation setting of phase 2
01 20ms													Bit[1:0]	
													00	10ms
													01	20ms
													10	30ms
11 40ms													11	40ms

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	OF	0	0	0	0	1	1	1	1		Set the scanning start position of the
0	1		<u>A7</u> 0	<u>A6</u> 0	A5 0	<u>A4</u> 0	<u>A3</u> 0	<u>A2</u> 0	<u>A1</u> 0	A0 A8	_ position	gate driver. The valid range is from 0 to 295. A[8:0] = 000h [POR] When TB=0: SCN [8:0] = A[8:0] When TB=1: SCN [8:0] = 295 - A[8:0]
												561 [0.0] - 275 - A[0.0]
0	0	10	0	0	0	1	0	0	0	0	Deep Sleep	Deep Sleep mode Control:
0	1		0	0	0	0	0	0	A1	AO	mode	A[1:0] : Description
												00 Normal Mode [POR]
												01 Enter Deep Sleep Mode 1
												11 Enter Deep Sleep Mode 2
												After this command initiated, the chip will enter Deep Sleep Mode, BUSY pad will keep output high. Remark: To Exit Deep Sleep mode, User required to send HWRESET to the driver
0	0	11	0	0	0	1	0	0	0	1	Data Entry	Define data entry sequence A[2:0] =
0	1		0	0	0	0	0	A2	A1	AO		O11 [POR] A [1:0] = ID[1:0] Address automatic increment / decrement setting The setting of incrementing or decrementing of the address counter can be made independently in each upper and lower bit of the address. O0 –Y decrement, X decrement, O1 –Y decrement, X decrement, 10 –Y increment, X increment, 11 –Y increment, X increment [POR] A[2] = AM Set the direction in which the address counter is updated automatically after data are written to the RAM. AM= 0, the address counter is updated in the X direction. [POR] AM = 1, the address counter is updated in the Y direction.
0	0	12	0	0	0	1	0	0	1	0	SW RESET	It resets the commands and parameters to their S/W Reset default values except R10h-Deep Sleep Mode During operation, BUSY pad will output high. Note: RAM are unaffected by this command.

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Command	De	escription
0	0	14	0	0	0	1	0	1	0	0	HV Ready Detection	HV ready detect A[7:0] = 00h [F The command r ANALOGEN=1. Refer to Register After this comm Ready detection BUSY pad will of detection. The detection re the Status Bit F	tion POR] required CLKEN=1 and er 0x22 for detail. hand initiated, HV h starts. utput high during result can be read from read (Command 0x2F).
0	1		0	A6	A5	A4	A3	A2	A1	AO		A[2:0]=m for L max HV ready of A[6:4]) x (m+1 HV ready detec after each cool detection will be is ready.	tion will be trigger down time. The e completed when HV eady detection, A[7:0]
0	0	15	0	0	0	1 0	0	1 A2	0 A1	1 A0	VCI Detection	2.3V A[2:0] : V A[2:0] 011 100 101 110 111 0ther The command r ANALOGEN=1 Refer to Registe this command i starts. BUSY pad will o detection. The detection reference	POR] , Detect level at CI level Detect VCI level 2.2V 2.3V 2.4V 2.5V 2.6V NA required CLKEN=1 and er 0x22 for detail. After nitiated, VCI detection utput high during esult can be read from tead (Command 0x2F).
0	0	18	0 A7	0 A6	0 A5	1 A4	1 A3	0 A2	0 A1	0 A0	Temperature Sensor Control	Temperature Se A[7:0] = 48h [f temperatrure se A[7:0] = 80h Ir	POR], external
0 0 0	0 1 1	1A	0 A11 A3	0 A10 A2	0 A9 A1	1 A8 A0	1 A7 0	0 A6 0	1 A5 0	0 A4 0	Temperature Sensor Control (Write to temperature register)	Write to tempo to temperature	erature register. Write register. [POR]
0 0 0	0 1 1	1B	0 A11 A3	0 A10 A2	0 A9 A1	1 A8 A0	1 A7 0	0 A6 0	1 A5 0	1 A4 0	Temperature Sensor Control (Read from temperature register)		perature register.

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	1C	0	0	0	1	1	1	0	0	Temperature	Write Command to External
0	1		A7	A6	A5	A4	A3	A2	A1	A0		temperature sensor.
0	1		B7	B6	B5	B4	B3	B2	B1	BO		A[7:0] = 00h [POR],
0	1		C7	C6	C5	C4	C3	C2	C1	CO	d to	B[7:0] = 00h [POR],
												aC[7:0] = 00h [POR], A[7:6]
											ture sensor)	A[7: 6] Select no of byte to be sent
												00 Address + pointer
												01 Address + pointer
												Address + pointer + 1st
												10 parameter +2nd pointer
												11 AddressA[5:0] – Pointer
												A[5:0] – Pointer Setting
												B[7:0] – 1st parameter
												C[7:0] – 2nd parameter
												The command required CLKEN=1.
												Refer to Register 0x22 for detail.
												After this command initiated, Write
												Command to external temperature
												sensor starts. BUSY pad will output high during operation.
												night during operation.
0	0	20	0	0	1	0	0	0	0	0	Master	Activate Display Update Sequence
											Activation	The Display Update Sequence Option
												is located at R22h.
												BUSY pad will output high during
												operation. User should not interrupt
												this operation to avoid corruption of
												panel images.
	-	01	<u> </u>	<u> </u>	-	6	<u> </u>	-	<u> </u>	-	Disalar	
0	0	21	0 A7	0 A6	1 A5	0 A4	0 A3	0 A2	0 A1	1 A0	Display Update Control 1	RAM content option for Display Update A[7:0] = 00h [POR]
0	1		A/	AO	AS	A4	A3	AZ	AI	AU	Control 1	A[7:4] Red RAM option
												0000 Normal
												0100 Bypass RAM content as 0
												1000 Inverse RAM content
												A[3:0] BW RAM option
												0000 Normal
												0100 Bypass RAM content as 0
												1000 Inverse RAM content

R/W#			D7	D6	D5	D4	D3	D2	D1	DO	Command		
0	0	22	0 A7	0 A6	1 A5	0 A4	0 A3	0 A2	1 A1	0 A0	Display Update	Display Update Sequence Option: Display Update Sequence Option: A[7:0] = FFh	
0			~/	70	73	74	73	72		70	Control 2	(POR)	I
											001111012		Paramet
												Enable Clock Signal, Then Enable ANALOG Then DISPLAY with DISPLAY Mode 1 Then Disable ANALOG	er(in C7
												Then Disable OSC Enable Clock Signal, Then Enable ANALOG Then DISPLAY with DISPLAY Mode 2 Then Disable ANALOG	CF
												Then Disable OSC Enable Clock Signal, Then Load LUT with DISPLAY Mode 1	90
												Enable Clock Signal, Then Load Temperature value from I2C Single Master Interface Then Load LUT with DISPLAY Mode 1	BO
												Enable Clock Signal, Then Load LUT with DISPLAY Mode 2	98
												Enable Clock Signal, Then Load Temperature value from I2C Single Master Interface Then Load LUT with DISPLAY Mode 2	B8
												Enable Clock Signal, Then Load LUT with DISPLAY Mode 1 To	91
												Enable Clock Signal, Then Load Temperature value from I2C Single Master Interface Then Load LUT with DISPLAY Mode 1 To Displace Clock Signal	B1
												Disable Clock Signal Enable Clock Signal, Then Load LUT with DISPLAY Mode 2 To Disable Clock Signal	99
												Enable Clock Signal, Then Load Temperature value from I2C Single Master Interface Then Load LUT with DISPLAY Mode 2 To	В9
												Disable Clock Signal Enable ANALOG Then DISPLAY with DISPLAY Mode 1 Then Disable ANALOG Then Disable OSC	47
												Enable ANALOG Then DISPLAY with DISPLAY Mode 2 Then Disable ANALOG Then Disable OSC	4F
												To Enable Clock Signal (CLKEN=1)	80
												To Enable Clock Signal, then Enable ANALOG (CLKEN=1, ANALOGEN=1)	CO
												Enable ANALOG Then DISPLAY with DISPLAY Mode 1	44
												Enable ANALOG Then DISPLAY with DISPLAY Mode 2	4C
												To DISPLAY with DISPLAY Mode 1	4
												To DISPLAY with DISPLAY Mode 2 To Disable ANALOG, then Disable Clock Signal (CLKEN=0, ANALOGEN=0)	0C 3
												To Disable Clock Signal (CLKEN=0)	1

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Command	Description
0	0	24	0	0	1	0	0	1	0	0	Write RAM (BW)	After this command, data entries will bewritten into the BW RAM until anothercommand is written. Address pointers willadvance accordingly For Write pixel: Content of Write RAM(BW) = 1 For Black pixel: Content of Write RAM(BW) = 0
0	0	26	0	0	1	0	0	1	1	0	Write RAM (RED)	After this command, data entries will bewritten into the RED RAM until anothercommand is written. Address pointers willadvance accordingly. For Red pixel: Content of Write RAM(RED) = 1 For non-Red pixel [Black or White]: Content of Write RAM(RED) = 0
0	0	27	0	0	1	0	0	1	1	1	Read RAM	After this command, data read on the MCU bus will fetch data from RAM [According to parameter of Register 41h to select reading RAM(BW) / RAM(RED)], until another command is written. Address pointers will advance accordingly. The 1st byte of data read is dummy data.
0	0	28	0	0	1	0	1	0	0	0	VCOM Sense	Enter VCOM sensing conditions and holdfor duration defined in 29h before readingVCOM value. The sensed VCOM voltage is stored in register The command required CLKEN=1 and ANALOGEN=1 Refer to Register 0x22 for detail. BUSY pad will output high during operation.
0	0	29	0	0	1	0	1	0	0	1	VCOM Sense	Stabling time between entering
0	1		0	1	0	0	A3	A2	A1	AO	Duration	VCOMsensing mode and reading acquired. A[3:0] = 09h [POR], duration = 10s. VCOM sense duration = (A[3:0]+1) sec

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Command		Des	scription	า	
0	0	2A	0	0	1	0	1	0	1	0	Program VCOM OTP	Program VCOM register into OTP The command required CLKEN=1. Refer to Register 0x22 for detail. BUSY pad will output high during operation.				
0	0	2B	0	0	1	0	1	0	1	1	Write Register	This con	nmand is	s used to	reduce	alitch
0	1		0	0	0	0	0	1	0	0	for				wo data b	
0	1		0	1	1	0	0	0	1	1	VCOM Control	D04h an commar		should b	e set for	this
0	0	2C	0	0	1	0	1	1	0	0	Write VCOM	Write V	COM reg	ster fron	n MCU	
0	1		A7	A6	A5	A4	A3	A2	A1	A0	register	interface	e A[7:0]	= 00h [l		,
												A[7:0]	VCOM	A[7:0]	VCOM	
												08h	-0.2	44h	-1.7	
												0Ch	-0.3	48h	-1.8	
												10h	-0.4	4Ch	-1.9	
												14h	-0.5	50h	-2	
												18h	-0.6	54h	-2.1	
												1Ch	-0.7	58h	-2.2	
												20h	-0.8	5Ch	-2.3	
												24h	-0.9	60h	-2.4	
												28h	-1	64h	-2.5	
												2Ch	-1.1	68h	-2.6	
												30h	-1.2	6Ch	-2.7	
												34h	-1.3	70h	-2.8	
												38h	-1.4	74h	-2.9	
												3Ch	-1.5	78h	-3	
												40h	-1.6	Other	NA	
0	0	2D	0 A7	0 A6	1 A5	0 A4	1 A3	1 A2	0 A1	1 A0	OTP Register Read for			r Display TP Selec	/ Option:	
1	1		B7	B6	B5	B4	B3	B2	B1	BO	Display Option	(Comma				
1	1		C7	C6	C5	C4	C3	C2	C1	CO		B[7:0]:			,	
1	1		D7	D6	D5	D4	D3	D2	D1	D0	-	(Comma				
1	1 1		E7 F7	E6 F6	E5 F5	<u>E4</u> F4	E3 F3	E2 F2	E1 F1	E0 F0	-			Display N		\sim
1	1		G7	G6	G5	<u>F4</u> G4	G3	G2	G1	GO	-	(Command 0x37, Byte B to Byte G) [5 bytes] G[7:0]~H[7:0]: Waveform Version (Command 0x37, Byte H to Byte K)				
1	1		H7	H6	H5	H4	H3	H2	H1	HO	1					n
1	1	-	17	16	15	14	13	12	11	10						
1	1		J7 דע	J6 V4	J5 VE	J4	J3	J2	J1	JO	-	[4 bytes]			
1	1		K7	K6	K5	K4	К3	K2	K1	KO						

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	2E	0	0	1	0	1	1	1	0	User ID Read	Read 10 Byte User ID stored in OTP:
1	1		A7	A6	A5	A4	A3	A2	A1	ÂŎ		A[7:0]]~J[7:0]: UserID (R38, Byte A
1	1		B7	B6	B5	B4	B3	B2	B1	BO	_	and Byte J) [10 bytes]
1	1		C7	C6	C5	C4	C3	C2	C1	CO	_	
1.	1		D7	D6	D5	D4	D3	D2	D1	DO	_	
1	1		E7	E6	E5	E4	E3	E2	E1	EO	_	
1	1		F7	F6	F5	F4	F3	F2	F1	FO		
1	1		G7	G6	G5	G4	G3	G2	G1	GO		
1	1		H7	H6	H5	H4	H3	H2	H1	HO		
1	1		17	16	15	14	13	12	11	10		
1	1		J7	J6	J5	J4	J3	J2	J1	JO	_	
		1	1			1	1	1 -	1 -		ų.	
0	0	2F	0	0	1	0	1	1	1	1	Status Bit Read	Read IC status Bit [POR 0x01]
1	1		0	0	A5	A4	0	A2	A1	AO		 A[5]: HV Ready Detection flag [POR=0] 0: Ready 1: Not Ready A[4]: VCI Detection flag [POR=0] 0: Normal 1: VCI lower than the Detect level A[3]: [POR=0] A[2]: Busy flag [POR=0] 0: Normal 1: BUSY A[1:0]: Chip ID [POR=01] Remark: A[5] and A[4] status are not valid after RESET, they need to be initiated by command 0x14 and command 0x15 respectively.
0	0	31	0	0	1	1	0	0	0	1	Load WS OTP	Load OTP of Waveform Setting The command required CLKEN=1. Refer to Register 0x22 for detail. BUSY pad will output high during operation.
	0										ha	
0	0	32	0	0	1	1	0	0	1	0	Write LUT	Write LUT register from MCU interface
0	1		A7	A6	A5	A4	A3	A2	A1	A0	register	[100 bytes], which contains the
0	1		B7	B6	B5	B4	B3	B2	B1	BO	_	content of VS [nX-LUT], TP #[nX],
0	1		:	:	:	:	:	:	:	:	4	RP#[n]).
0	1											Refer to Session 6.7 Waveform

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Command	Description
0	0	34	0	0	1	1	0	1	0	0	CRC calculation	CRC calculation command for OTP content validation. For details, please refer to SSD1675B application note. BUSY pad will output high during operation.
0	0	35	0	0	1	1	0	1	0	1	CRC Status	CRC Status Read
1	1	35	A15	A14	A13	A12	A11	A10	A9	A8	Read	A[15:0] is the CRC read out value
1	1		A7	A14 A6	ATS A5	A12 A4	ATT A3	A10 A2	A9 A1	AO	Reau	
- 1		1 1	Α/	AU	73	~~	73	A2		AU		
0	0	36	0	0	1	1	0	1	1	0	Program OTP selection	Program OTP Selection according to the OTP Selection Control [R37h and R38h] The command required CLKEN=1. Refer to Register 0x22 for detail. BUSY pad will output high during operation.
0	1	37	0	0	1	1	0	1	1	1	Write Register	Write Register for Display Option
0	1	37	0	0	0	0	0	0	0	0	for	B[7:0] Display Mode for WS[7:0]
0	1		B7	B6	B5	B4	B3	B2	B1	BO	Display Option	C[7:0] Display Mode for WS[15:8]
0	1		C7	C6	C5	C4	C3	C2	C1	CO		D[7:0] Display Mode for WS[23:16]
0	1		D7	D6	D5	D4	D3	D2	D1	D0	-	E[7:0] Display Mode for WS[23:10] E[7:0] Display Mode for WS[31:24]
0	1		E7	E6	E5	E4	E3	E2	E1	EO	_	F[3:0] Display Mode for WS[31:24]
0	1		 F7	F6	F5	 F4	 F3	F2	F1	FO		Display Mode 1 [POR]
0	1		G7	G6	G5	G4	G3	G2	G1	GO		1: Display Mode2
0	1		H7	H6	H5	H4	H3	H2	H1	HO	-	F[6]: PingPong for Display Mode 2
0	1		17	16	15	14	13	12	11	10		0: RAM ping-pong disable [POR]
0	1		J7	J6	J5	J4	J3	J2	J1	OL		 RAM ping-pong enable G[7:0]~J[7:0] module ID /waveform version. Remarks: A[7:0]~J[7:0] can be stored in OTP RAM ping-pong function is not support for Display Mode 1
0	0	38	0	0	1	1	1	0	0	0	Write Register	Write Register for User ID
0	1		A7	A6	A5	A4	A3	A2	A1	A0	for User	A[7:0]]~J[7:0]: UserID [10 bytes]
0	1		B7	B6	B5	B4	B3	B2	B1	B0	ID	Remarks: A[7:0]~J[7:0] can be
0	1		C7	C6	C5	C4	C3	C2	C1	CO		stored in OTP
0	1		D7	D6	D5	D4	D3	D2	D1	D0		
0	1		E7	E6	E5	E4	E3	E2	E1	EO		
0	1		F7	F6	F5	F4	F3	F2	F1	FO		
0	1		G7	G6	G5	G4	G3	G2	G1	G0		
0	1		H7	H6	H5	H4	H3	H2	H1	HO		
0	1		17	16	15	14	13	12	11	10		
0	1		J7	J6	J5	J4	J3	J2	J1	JO		

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Command	Description
0	0	39	0	0	1	1	1	0	0	1	OTP program	OTP program mode OTP program
0	1		0	0	0	0	0	0	0	0	mode	mode
												A[1:0] = 11: Internal generated OTP A[1:0] = 11: Internal generated OTP
												programming voltage
												Remark: User is required to EXACTLY
0	0	3A	0	0	1	1	1	0	1	0	Sat dummy ling	Set number of dummy line period
0	1	SA	0	A6	A5	A4	A3	A2	A1	AO	period	A[6:0] = 30h [POR]
-			-									A[6:0]: Number of dummy line period
												in term of TGate
												Available setting 0 to 127.
0	0	3B	0	0	1	1	1	0	1	1	Set Gate line	Set Gate line width (TGate) A[3:0] =
0	1	30	0	0	0	0	A3	A2	A1	AO	width	1010 [POR]
												Remark: Default value will give 50Hz
												Frame frequency under 48 dummy
												line pulse setting.
Frame	Frequen	су		neter c	of	Param	eter o	f 0x3B				
[Hz] 25			0x3A 0x29			0x0E			-			
30			0x46			0x0D			-			
35			0x48			0x0D			-			
40			0x48			0x0C			-			
45			0x28			0x0C			-			
50			0x0F			0x0C			-			
55			0x37			0x0B			-			
60			0x21			0x0B			-			
65			0x0E			0x0B			-			
70			0x22			0x0A						
75			0x11			0x0A						
80			0x03			0x0A			-			
85			0x17			0x09						
90			0x0A			0x09						
95			0x26			80x0						
100			0x1A			0x08						
105			0x0E			0x08						
110			0x04			0x08						
115			0x1D			0x07						
120			0x13			0x07						
125			0x0A			0x07						
130			0x01			0x06						
135			0x22			0x06						
145			0x11			0x06						
150			0x0A			0x06			-			
155			0x03			0x06			-			
160			0x1C			0x05			-			
165			0x15			0x05			-			
170			Ox0E			0x05			-			
175			0x07			0x05			-			
180			0x01			0x05			-			
185			0x21			0x04			-			
190			0x1B			0x04			-			
195			0x15			0x04			-			
200			0x0F			0x04 n resolu			-			

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description			
0	0	3C	0	0	1	1	1	1	0	0	Border	Select border waveform for VBD			
0	1		A7	A6	A5	A4	A3	A2	A1	A0	Waveform Control	A [7:6] :S	COh [POR], set VBD as HIZ. elect VBD option		
												A[7:6]	Select VBD as		
												00	GS Transition,Defined in A[1:0]		
												01	Fix Level,Defined in A[5:4]		
												10	VCOM		
												11[POR]	HiZ		
												A [5:4] Fix A[5:4]	< Level Setting for VBD		
												00[POR]	VSS		
												01	VSH1		
												10	VSL		
												11	VSH2		
												A [1:0] GS Transition setting for VBD			
												A[1:0]	VBD Transition		
												00[POR]	LUTO		
												01	LUT1		
												10	LUT2		
												11	LUT3		
	1			1							L				
0	0	41	0	1	0	0	0	0	0	1	Read RAM	Read RAM			
0	1		0	0	0	0	0	0	0	AO	Option	A[0] = 0 [F	AM corresponding to 24h		
													AM corresponding to 26h		
0	0	44	0	1	0	0	0	1	0	0	Set RAM X -	Specify th	e start/end positions of the		
0	1	44	0	0	A5	A4	A3	A2	A1	AO	address Start /		dress in the X direction by		
0	1		0	0	B5	B4	B3	B2	B1	BO	End position	an address	s unit for RAM		
													SA[5:0], XStart, POR = 00h FA[5:0], XEnd, POR = 13h		
	0	4 -	0	1			0	4	0	1	Cat Dars V	-			
0	0	45	0 A7	1 A6	0 A5	0 A4	0 A3	1 A2	0 A1	1 A0	Set Ram Y- address Start /		e start/end positions of the ddress in the Y direction by		
0	1		0	0	0	0	0	0	0	A8	End position		s unit for RAM		
0	1		B7	B6	B5	B4	B3	B2	B1	B0		A[8:0]: YS	SA[8:0], YStart, POR = 000h		
0	1		0	0	0	0	0	0	0	B8		B[8:0]: YE	A[8:0], YEnd, POR = 127h		

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Command	Description				
0	0	46	1	0	0	0	0	1	1	0	Auto Write RED					
0	1		A7	A6	A5	A4	A3	A2	A1	A0	RAM Auto Write RED RAM	Pattern A[7:0] = 00h [POR] Auto Write RED RAM for Regular Pattern A[7:0] = 00h [POR]				
												A[6:4]:	Step Hei	ep value, ght, POR 1 in Y-dire		
												accordin				
												A[6:4]	-	A[6:4]	Height	
												000	8	100	128	
												001	16	101	256	
												010	32	110	296	
												011	64	111	NA	
														lth, POR= lth, POR=		
												A[2:0]	Width	A[2:0]	Width	
												000	8	100	128	
												001	16	101	160	
												010	32	110	NA	
												011	64	111	NA	
												BUSY pa operatio		tput high	during	
0	0 1	47	0 A7	1 A6	0 A5	0 A4	0 A3	1 A2	1 A1	1 A0	RAM for	Pattern A A[7]: Th A[6:4]: Step of a	Auto Write B/W RAM for Regular Pattern A[7:0] = 00h [POR] A[7]: The 1st step value, POR = 0 A[6:4]: Step Hieght, POR= 000 Step of alter RAM in Y-direction			
												accordin			11-1-1-1	
												A[6:4]	Height 8	A[6:4]	Ŭ	
												000	8	100	128 256	
												010	32	101	296	
												010	64	111	NA	
												A[2:0]:	Step Wid	ith, POR= ith, POR=	= 000	
												A[2:0]	Width	A[2:0]	Width	
												000	8	100	128	
												001	16	101	160	
												010	32	110	NA	
												011	64	111	NA	
												During c output h		, BUSY p	ad will	

R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	4E	0	1	0	0	1	1	1	0	Set RAM X	Make initial settings for the RAM X
0	1		0	0	A5	A4	A3	A2	A1	AO	address X	address in the address counter (AC)
											address	address in the address counter (AC)
				r						r	1	
0	0	4F	0	1	0	0	1	1	1	1	Set RAM Y	Make initial settings for the RAM Y
0	1		A7	A6	A5	A4	A3	A2	A1	AO	address	address in the address counter (AC)
				_		_	Α				counter	A[8:0]: 000h [POR].
0	1		0	0	0	0	0	0	0	A8		
	-			-					-		1	
0	0	74	0	1	1	1	0	1	0	0	Set Analog	A[7:0]: 54h [POR]
0	1		A7	A6	A5	A4	A3	A2	A1	A0	Block Control	
							Α					
	-					-		1		-	T	
0	0	7E	0	1	1	1	1	1	1	0	Set Digital	A[7:0]: 3Bh [POR]
0	1		A7	A6	A5	A4	A3	A2	A1	AO	Block Control	
							Α					
	-			-		-						
0	0	7F	0	1	1	1	1	1	1	1	NOP	This command is an empty command;
												it does not have any effect on the
												display module.
												However it can be used to terminate
												Frame Memory Write or Read
												Commands.

6. Optical characteristics

6.1 Specifications

Measurements are made with that the illumination is under an angle of 45 degrees, the detection is perpendicular unless otherwise specified. T=25 $^{\circ}$ C

					I=2	.5 C	
SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT	Note
R	Reflectance	White	30	35	-	%	Note 6-1
Gn	2Grey Level	-	-	DS+(WS-DS)×n(m-1)	-	L*	-
CR	Contrast Ratio	indoor	-	10	-	-	-
Panel's life	-	0°C∼30°C		5years	-	-	Note 6-2

M:2

WS : White state, DS : Dark state

Note 16-1 : Luminance meter : Eye - One Pro Spectrophotometer ;

Note 16-2: We guarantee display quality from $0^{\circ}C \sim 30^{\circ}C$ generally, If operation ambient temperature from $0 \sim 50^{\circ}C$, w ill Offer special waveform by Ingcool

We don't guarantee 5 years pixels display quality for humidity below 45%RH or above 70%RH;

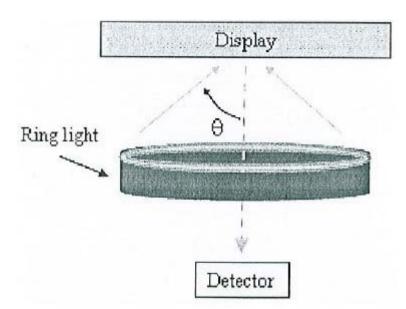
Suggest Updated once a day;

6.2 Definition of contrast ratio

The contrast ratio (CR) is the ratio between the reflectance in a full white area (R1) and the reflectance in a dark area (Rd)():

R1: white reflectance Rd: dark reflectance

CR = R1/Rd

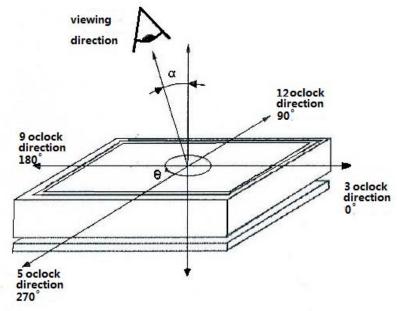


6.3 Reflection Ratio

The reflection ratio is expressed as :

 $R = Reflectance Factor_{white board} \qquad x (L_{center} / L_{white board})$

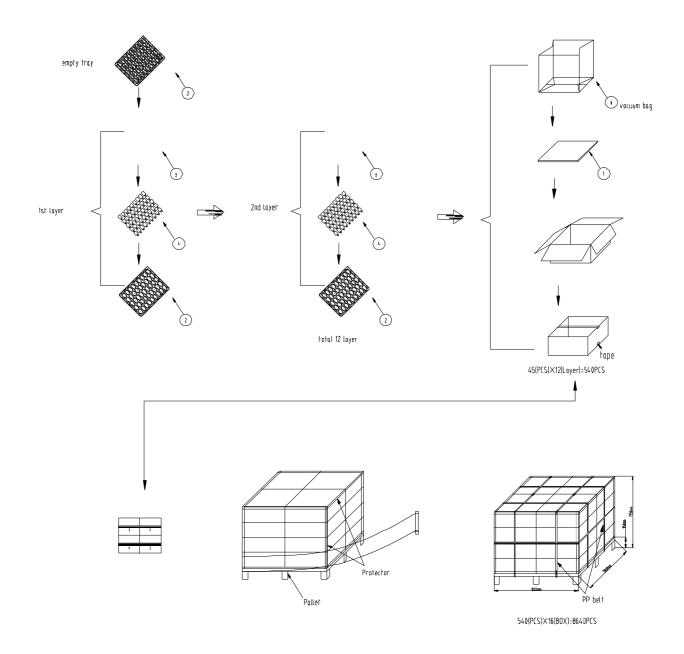
L _{center} is the luminance measured at center in a white area (R=G=B=1). L _{white board} is the luminance of a standard white board. Both are measured with equivalent illumination source. The viewing angle shall be no more than 2 degrees.



7. Point and line standard

Shipment Insp	ection Standard					
Equipment: Elec	ctrical test fixture, Po	int gauge				
Outline dimension	29.2(H)×59.2 (V) ×1.05(D)	Unit: mm	Part-A	Active area	Part-B	Border area
Environment	Temperature	Humidity	Illuminance	Distance	Time	Angle
	19℃~25℃	55%±5%RH	800~1300Lux	300 mm	35Sec	
Defet type	Inspection method	Standard	•	Part-A		Part-B
Spot	Electric Display	D≤0.25 mm		Ignore		Ignore
		0.25 mm <d≤0.< td=""><td>.4 mm</td><td>N≤4</td><td></td><td>Ignore</td></d≤0.<>	.4 mm	N≤4		Ignore
		D>0.4 mm		Not Allow		Ignore
Display unwork	Electric Display	Not	Allow	Not Allow		Ignore
Display error	Electric Display	Not	Allow	Not Allow		Ignore
Scratch or line	Visual/Film card	L≤2 mm, W≤0.	2 mm	Ignore		Ignore
defect(include		2.0mm <l≤5.< td=""><td>0mm,0.2<</td><td>N≤2</td><td>Ignore</td></l≤5.<>	0mm,0.2<	N≤2	Ignore	
dirt)		W≤0.3mm,				-
		L>5 mm, W>0	0.3 mm	Not Allow		Ignore
PS Bubble	Visual/Film card	D≤0.2mm		Ignore	Ignore	
		0.2mm≤D≤0.	35mm & N≤4	N≤4		Ignore
		D>0.35 mm		Not Allow		Ignore
Corner /Edge chipping	Visual/Film card	chipping) X≤1mm,Y≤1	.4mm, Do not aff mm, Do not aff er chipping) Ign	ect the elect		circuit (Edge
Remark	1.Cannot be defect	& failure cause	e by appearance	e defect;		
	2.Cannot be larger	size cause by a	appearance defe	ect;		
	L=long	W=w	ide D=point si	ze N=Defe	ects NO	

8. Packing



9. Precautions

- (1) Do not apply pressure to the EPD panel in order to prevent damaging it.
- (2) Do not connect or disconnect the interface connector while the EPD panel is in operation.
- (3) Do not touch IC bonding area. It may scratch TFT lead or damage IC function.
- (4) Please be mindful of moisture to avoid its penetration into the EPD panel, which may cause damage during operation.
- (5) If the EPD Panel / Module is not refreshed every 24 hours, a phenomena known as "Ghosting" or "Image Sticking" may occur. It is recommended to refreshed the ESL / EPD Tag every 24 hours in use case. It is recommended that customer ships or stores the ESL / EPD Tag with a completely white image to avoid this issue
- (6) High temperature, high humidity, sunlight or fluorescent light may degrade the EPD panel's performance. Please do not expose the unprotected EPD panel to high temperature, high humidity, sunlight, or fluorescent for long periods of time.